A110a0

NSN 5961-01-069-8084 Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-069-8084
Inclosure Material:
Metal
Overall Length:
1.810 inches
Mounting Facility Quantity:
1
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
Between 1.031 inches and 1.063 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
1400.0 nonrepetitive peak reverse voltage, peak total value
Current Rating Per Characteristic:
110.00 amperes on-state current, rms total
Power Rating Per Characteristic:
2.0 watts average gate power-forward
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius junction
Test Data Document:
05869-719172 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
No
Fiig: